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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. Of: TANABE et al.
Serial No.: 09/612,551
Filed: July 7, 2000
For: SEMICONDUCTOR THIN FILM FORMING SYSTEM
Group: 1725
Examiner: GEOFFREY S. EVANS DOCKET: NEC WNZ-2212
Assistant Commissioner of Patents and Trademarks
Washington, D.C. 20231

AMENDMENT D

Dear Sir:

The following Amendment is being filed in response to the Official Action mailed December 5, 2002.

Please amend the Application as follows:

IN THE TITLE:

Please amend the title to read as follows:

--A SYSTEM FOR THE FORMATION OF A SILICON THIN FILM AND A
SEMICONDUCTOR-INSULATING FILM INTERFACE--

IN THE CLAIMS:

Please amend claims 1 and 17-22 to read as follows:

1. (Twice Amended) A semiconductor thin film forming method comprising:
modifying a predetermined region of a semiconductor thin film by exposing the
semiconductor thin film to a projected light patterned through plural patterns formed on a photo
mask; and

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